

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1	10/825301	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/14 13:35
S2	1100	(349/5).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/14 13:37
S3	99769	"thin film transistor" TFT	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/14 14:14
S4	23415	"lightly doped drain" LDD	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/14 13:38
S5	1920	("thin film transistor" TFT) near6 (P-type)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/14 13:41
S6	109	S4 near6 S5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/14 13:41
S7	0	S2 and S6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/14 13:41
S8	10	349\$.ccls. and S6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/14 14:15

S9	1308	("thin film transistor" TFT) near6 "leakage current"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/14 14:15
S10	37	("thin film transistor" TFT) near6 "leakage current" near6 (black or shield)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/14 14:15
S11	25	349\$.ccls. and S10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/14 14:15